- Single-Chip RS-232 Interface for IBM[™] PC[™] Compatible Serial Port
- Designed to Transmit and Receive 4-μs Pulses (Equivalent to 256 kbit/s)
- Standby Power Is Less Than 750 μW Maximum
- Wide Supply-Voltage Range . . . 4.75 V to 15 V
- Driver Output Slew Rates Are Internally Controlled to 30-V/µs Maximum
- RS-232 Bus-Pin ESD Protection Exceeds:
 - 15 kV, Human-Body Model
 - 8-kV IEC1000-4-2, Contact
 - 15-kV IEC1000-4-2, Air Gap
- Receiver Input Hysteresis . . . 1000 mV Typical
- Three Drivers and Five Receivers Meet or Exceed the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Complements the SN75LP196
- One Receiver Remains Active During WAKE-UP Mode (100 μA Maximum)
- Matches the Flow-Through Pinout of the Industry-Standard SN75185, SN75C185, and SN75LP185, With Additional Control Pins
- Package Options Include Plastic Shrink Small-Outline (DB), Small-Outline (DW), Thin Shrink Small-Outline (PW), and Standard Plastic (NT) DIPs

description

The SN75LPE185 is a low-power bipolar device containing three drivers and five receivers, with 15-kV ESD protection on the bus pins, with respect to each other. Bus pins are defined as those pins that tie directly to the serial-port connector, including GND. The pinout matches the flow-through design of the industry-standard SN75185, SN75C185, and SN75LP185, with the addition of four pins for control signals. The flow-through pinout of the device allows easy interconnection of the UART and serial-port connector of the IBM PC compatibles. The SN75LPE185 provides a rugged, low-cost solution for this function with the combination of bipolar processing and 15-kV ESD protection.

The SN75LPE185 has an internal slew-rate control to provide a maximum rate of change in the output signal of 30 V/ μ s. The driver output swing is clamped at \pm 6 V to enable the higher data rates associated with this device and reduce EMI emissions. Although the driver outputs are clamped, the outputs can handle voltages up to \pm 15 V without damage.

The device has flexible control options for power management when the serial port is inactive. A common disable for all of the drivers and receivers is provided with the active-low enable (EN) input. The mode control (MODE) input selects between the STANDBY and WAKE-UP modes. With a low-level input on the MODE pin and a high-level input on the EN pin, one receiver remains active while the remaining drivers and receivers are



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NC - No internal connection

description (continued)

disabled to implement the WAKE-UP mode. With a high-level input on both the MODE and EN pins, all drivers and receivers are disabled to implement the STANDBY mode. The outputs of the drivers are in a high-impedance state when the device is powered off. To ensure the outputs of the receivers are in a known output level (as listed in the *Application Information* section of this data sheet) when the device is powered off, in STANDBY, or WAKE-UP mode, external pullup/pulldown circuitry must be provided. All the logic inputs accept 3.3-V or 5-V input signals.

The SN75LPE185 complies with the requirements of TIA/EIA-232-F and ITU v.28 standards. These standards are for data interchange between a host computer and peripheral at signaling rates up to 20 kbit/s. The switching speeds of the SN75LPE185 support rates up to 256 kbit/s.

The SN75LPE185 is characterized for operation from 0°C to 70°C.

_	DRIVERS						
INPUT DA	ENABLE EN	OUTPUT DY					
Х	Н	Z					
Н	L	L					
L	L	н					
Open	L	L					
Н	Open	L					
L	Open	Н					

Function Tables

H = high level, L = low level,

X = irrelevant, Z = high impedance (off)

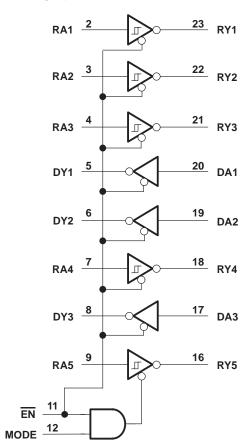
INP	JTS	ENABLE INPUTS		OUTF	PUTS
RA1–RA4	RA5	EN	MODE	RY1–RY4	RY5
Н	Н	L	Х	L	L
L	L	L	Х	н	н
Х	Н	Н	L	Z	L
Х	L	Н	L	Z	Н
Х	Х	Н	н	Z	Z
Open	Open	L	Х	Н	Н
н	Н	L	Open	L	L
L	L	L	Open	Н	Н
Х	Н	Н	Open	Z	L
Х	L	Н	Open	Z	н
н	Н	Open	х	L	L
L	L	Open	Х	Н	Н

RECEIVERS

H = high level, L = low level, X = irrelevant, Z = high impedance (off)



functional logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Positive supply voltage range: V _{CC} (see Note 1) V _{DD} (see Note 1)	
Negative supply voltage range, V _{SS} (see Note 1)	
Receiver input voltage range, V _I (RA)	
Driver input voltage range, V _I (DA, EN, MODE)	
Receiver output voltage range, V _O (RY)	
Driver output voltage range, $V_O(DY)$	
Electrostatic discharge, bus pins: Machine model (see Note 2)	
Human-body model (see Note 2)	Class 3, 15 kV
IEC1000-4-2: contact	Class 3, 8 kV
IEC1000-4-2: airgap	Class 3, 15 kV
Electrostatic discharge, all pins: Human-body model (see Note 2)	Class 3, 5 kV
Machine model (see Note 2)	Class 3, 200 V
Package thermal impedance, θ_{JA} (see Note 3): DB package	104°C/W
DW package	81°C/W
NT package	67°C/W
PW package	120°C/W
Storage temperature range, T _{stg}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to network ground terminal unless otherwise noted.

2. Per MIL-STD-883 Method 3015.7

3. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

				MAX	UNIT
Supply voltage, V _{CC} (see Note 4)		4.75	5	5.25	V
Supply voltage, V _{DD}		9	12	15	V
Supply voltage, V _{SS}		-9	-12	-15	V
High level input voltage, VIH	DA, EN, MODE	2			V
Low level input voltage, VIL	DA, EN, MODE			0.8	V
Receiver input voltage range, VI	RA	-25		25	V
High level output current, I _{OH}	RY			-1	mA
Low level output current, I _{OL}	RY			2	mA
Operating free air temperature, T _A		0		70	°C

NOTE 4: V_{CC} cannot be greater than V_{DD}.



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supply currents over the recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
		No load,	$V_{DD} = 9 V$, $V_{SS} = -9 V$, \overline{EN} at GND, See Note 5			1000	
ICC	Supply current for V _{CC}	All inputs at	$V_{DD} = 12 \text{ V}, \text{ V}_{SS} = -12 \text{ V}, \overline{\text{EN}} \text{ at GND}$			1000	μA
		minimum V _{OH} or maximum V _{OI}	EN, MODE at V _{CC}			650	
			EN at V _{CC} , MODE at GND			700	
		No load,	$V_{DD} = 9 V$, $V_{SS} = -9 V$, \overline{EN} at GND, See Note 5			800	
IDD	Supply current for VDD	All inputs at minimum VOH	$V_{DD} = 12 \text{ V}, \text{ V}_{SS} = -12 \text{ V}, \overline{\text{EN}} \text{ at GND}$			800	μA
		or maximum VOH	EN, MODE at V _{CC}			20	
			EN at V _{CC} , MODE at GND			20	
		No load,	$V_{DD} = 9 V$, $V_{SS} = -9 V$, \overline{EN} at GND, See Note 5			-625	
ISS	Supply current for VSS	All inputs at minimum VOH	$V_{DD} = 12 \text{ V}, \text{ V}_{SS} = -12 \text{ V}, \overline{\text{EN}} \text{ at GND}$			-625	μA
		or maximum V _{OL}	EN, MODE at V _{CC}			-50	
			EN at V _{CC} , MODE at GND			-50	

NOTE 5: Minimum RS-232 driver output voltages are not attained with ±5-V supplies.

driver electrical characteristics over the recommended operating conditions (unless otherwise noted)

	PARAMETER	TE	ST CONDITIONS	MIN	TYP	MAX	UNIT
Varia	High-level	VI = 0.8 V, RL = 3 kΩ,	$V_{DD} = 9 V$, $V_{SS} = -9 V$, \overline{EN} at GND, See Note 5	5	5.8	6.6	V
Vон	output voltage	See Figure 1	V_{DD} = 12 V, V_{SS} = -12 V, EN at GND, See Note 6	5	5.8	6.6	v
Ve	Low-level	V _I = 2 V, R _L = 3 K,	$V_{DD} = 9 V$, $V_{SS} = -9 V$, \overline{EN} at GND, See Note 5	-5	-5.8	-6.9	V
VOL	output voltage	See Figure 1	$\frac{V_{DD}}{EN}$ = 12 V, V _{SS} = -12 V, EN at GND, See Note 6	-5	-5.8	-6.9	v
Ιн	High-level input current	VI at V _{CC}				1	μΑ
١ _{IL}	Low-level input current	V _I at GND				-1	μA
I _{OZ}	High-impedance output current	V _{CC} = 5 V,	V_{DD} = 12 V, V_{SS} = -12 V, -5 V \leq V _O \leq 5 V			±100	μΑ
IOS(H)	Short-circuit high-level output current	$V_{O} = GND \text{ or } V_{SS},$	See Figure 2 and Note 7		-30	-55	mA
IOS(L)	Short-circuit low-level output current	$V_{O} = GND \text{ or } V_{SS},$	See Figure 2 and Note 7		30	55	mA
r _o	Output resistance	$V_{DD} = V_{SS} = V_{CC} = 0,$	$V_{O} = 2 V$	300			Ω

NOTES: 5. Minimum RS-232 driver output voltages are not attained with \pm 5-V supplies.

6. Maximum output swing is limited to ±5.5 V to enable the higher data rates associated with this device and to reduce EMI emissions.

7. Not more than one output should be shorted at one time.



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driver switching characteristics over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
^t PHL	Propagation delay time, high-to low-level output	$P_{1} = 3 k_{0} t_{0} \overline{7} k_{0}$	C _I = 15 pF, See Figure 1	300	800	1600	ns
^t PLH	Propagation delay time, low-to high-level output	$R_L = 3 k\Omega$ to 7 k Ω ,	CL = 15 pr, See Figure 1	300	800	1600	115
^t PZL	Driver output-enable time to low-level output	$R_L = 3 k\Omega$ to 7 kΩ,			50	100	
^t PZH	Driver output-enable time to high-level output	C _L = 15 pF	See Figures 1, 6, and Note 6	50		100	μs
^t PLZ	Driver output-disable time from low-level output	$R_1 = 3 k\Omega$ to 7 k Ω ,	STANDBY or WAKE-UP modes,		50	100	
^t PHZ	Driver output-disable time from high-level output	C _L = 15 pF	See Figures 1, 6, and Note 6		50	100	μs
			Using 10%-to-90% transition region, Driver speed = 250 kbit/s $C_L = 15 \text{ pF}$	375		2240	
t	Transition time,	$V_{CC} = 5 V,$ $V_{DD} = 12 V,$ $V_{SS} = -12 V,$	Using \pm 3-V transition region, Driver speed = 250 kbit/s C _L = 15 pF	200		1500	ns
^t TLΗ	low-to high-level output	$R_L = 3 k\Omega$ to 7 k Ω , See Figure 1 and Note 6	Using \pm 2-V transition region, Driver speed = 250 kbit/s C _L = 15 pF	133		1000	115
			Using \pm 3-V transition region, Driver speed = 125 kbit/s C _L = 2500 pF			2750	
			Using 10%-to-90% transition region, Driver speed = 250 kbit/s $C_L = 15 \text{ pF}$	375		2240	
4	Transition time,	$V_{CC} = 5 V,$ $V_{DD} = 12 V,$	Using \pm 3-V transition region, Driver speed = 250 kbit/s C _L = 15 pF	200		1500	
ťΤΗL	high-to low-level output	$V_{SS} = -12 \text{ V},$ RL = 3 k Ω to 7 k Ω See Figure 1 and Note 6	Using \pm 2-V transition region, Driver speed = 250 kbit/s C _L = 15 pF	133		1000	ns
			Using \pm 3-V transition region, Driver speed = 125 kbit/s C _L = 2500 pF			2750	
SR	Output slew rate	$V_{CC} = 5 V, \\ V_{DD} = 12 V, \\ V_{SS} = -12 V, \\ R_L = 3 k\Omega \text{ to } 7 k\Omega, \\ C_L = 15 \text{ pF}, \\ \text{See Note 6}$	Using ±3-V transition region, Driver speed = 0 to 250 kbit/s	4	20	30	V/µs

NOTE 6: Maximum output swing is limited to ±5.5 V to enable the higher data rates associated with this device and to reduce EMI emissions.



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receiver electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
VIT+	Positive-going input threshold voltage	See Figure 3		1.6	2	2.55	V
V _{IT} –	Negative-going input threshold voltage	See Figure 3		0.6	1	1.45	V
V _{HYS}	Input hysteresis, V _{IT+} – V _{IT} –	See Figure 3		600	1100		mV
VOH	High-level output voltage	I _{OH} = -1 mA,		2.5	3.9		V
VOL	Low-level output voltage	I _{OL} = 2 mA,			0.33	0.5	V
lu i	High-level input current	V _I = 3 V		0.43	0.6	1	mA
ŀΗ	High-level input current	V _I = 25 V		3.6	5.1	8.3	mA
	Low-level input current	$V_{I} = -3 V$		-0.43	-0.6	-1	A
ΙL	Low-level input current	V _I = -25 V		-3.6	-5.1	-8.3	mA
IOS(H)	Short-circuit high-level output current	$V_{O} = 0,$	See Figure 5 and Note 7			-20	mA
IOS(L)	Short-circuit low-level output current	$V_{O} = V_{CC},$	See Figure 5 and Note 7			20	mA
I _{OZ}	High-impedance output current	V _{CC} = 0 or 5 V,	$0.3 \text{ V} \le \text{V}_O \le \text{V}_{CC}$			±100	μΑ
R _{IN}	Input resistance	$V_I = \pm 3 V \text{ to } \pm 25 V$	1	3	5	7	kΩ

NOTE 7: Not more than one output should be shorted at one time.

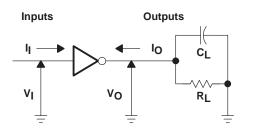
receiver switching characteristics over recommended operating free-air temperature range (unless otherwise noted)

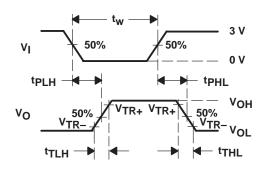
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
^t PHL	Propagation delay time, high- to low-level output			400	900	ns
^t PLH	Propagation delay time, low- to high-level output			400	900	115
^t TLH	Transition time low- to high-level output			200	500	ns
^t THL	Transition time high- to low-level output			200	400	115
^t SK(P)	Pulse skew tpLH - tpHL	STANDBY mode		200	425	ns
tPZL	Receiver output-enable time to low-level output	C _L = 50 pF,		50	100	μs
^t PZH	Receiver output-enable time to high-level output	See Figures 4 and 7		50	100	μs
^t PLZ	Receiver output-disable time from low-level output			50	100	
^t PHZ	Receiver output-disable time from high-level output			50	100	μs
^t PHL	Propagation delay time, high- to low-level output (WAKE-UP mode)			500	1500	ns
^t PLH	Propagation delay time, low- to high-level output (WAKE-UP mode)			500	1500	115



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PARAMETER MEASUREMENT INFORMATION





- NOTES: A. The pulse generator has the following characteristics: For $C_L < 1000 \text{ pF}$: $t_W = 4 \text{ }\mu\text{s}$, PRR = 250 kbit/s, $Z_O = 50 \Omega$, $t_r = t_f < 50 \text{ ns}$. For $C_L = 2500 \text{ pF}$: $t_W = 8 \mu\text{s}$, PRR = 125 kbit/s, $Z_O = 50 \Omega$, $t_r = t_f < 50 \text{ ns}$.
 - B. C₁ includes probe and jig capacitance.

Figure 1. Driver Parameter Test Circuit and Waveform

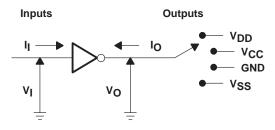
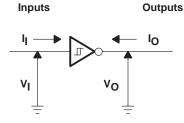
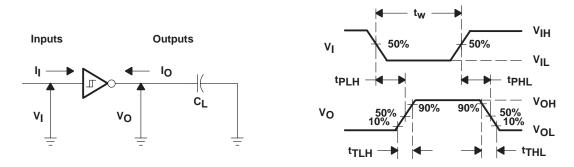


Figure 2. Driver IOS Test







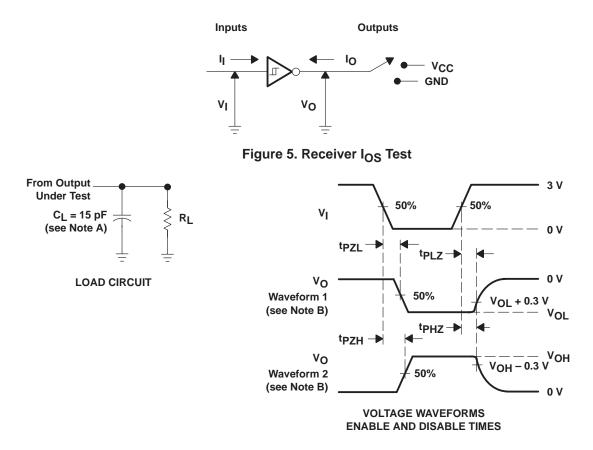
NOTES: A. The pulse generator has the following characteristics: $t_W = 4 \mu s$, PRR = 250 kbit/s, $Z_O = 50 \Omega$, $t_f = t_f < 50 ns$. B. C₁ includes probe and jig capacitance.

Figure 4. Receiver Parameter Test Circuit and Waveform



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PARAMETER MEASUREMENT INFORMATION

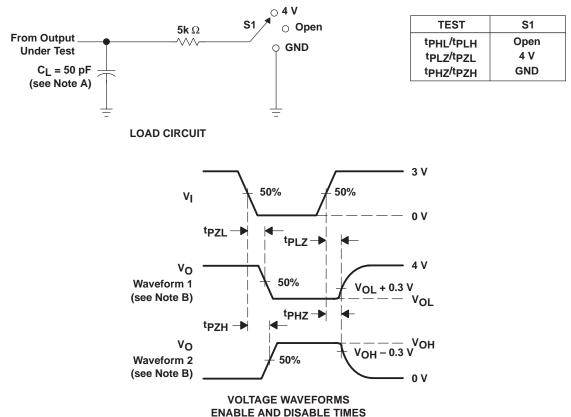


- NOTES: A. CL includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, $t_f = t_f < 50 ns$.
 - D. The outputs are measured one at a time with one transition per measurement.

Figure 6. Driver 3-State Parameter Circuit and Voltage Waveforms



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PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, $t_r = t_f < 50 ns$.

D. The outputs are measured one at a time with one transition per measurement.

Figure 7. Receiver 3-State Parameter Test Circuit and Voltage Waveforms



APPLICATION INFORMATION

receiver output states

RECEIVER KNOWN OUTPUT STATES DURING POWER-DOWN, STANDBY, OR WAKE-UP MODES						
RECEIVER NUMBER SIGNAL NAME RECEIVER OUTPUT						
RY1	DCD	HIGH				
RY2	DSR	HIGH				
RY3	RX	LOW				
RY4	CTS	HIGH				
RY5	RI	HIGH				

fault protection during power down

Diodes placed in series with the V_{DD} and V_{SS} leads protect the SN75LPE185 in the fault condition, in which the device outputs are shorted to \pm 15 V and the power supplies are at low voltage and provide low-impedance paths to ground.

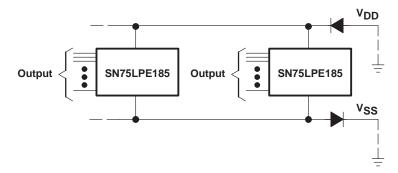


Figure 8. Power-Supply Protection to Meet Power-Off Fault Conditions of TIA/EIA-232-F



APPLICATION INFORMATION

WAKE-UP mode

While in the WAKE-UP mode, all the drivers and receivers of the SN75LPE185 device are in the high-impedance state, except for receiver 5, which can be used as a Ring Indicator function. In this mode, the current drawn from the power supplies is low, to conserve power.

In today's PCs, board designers are becoming more concerned about power consumption. The flexibility of the SN75LPE185 during WAKE-UP mode allows the designer to operate the device at auxiliary power-supply voltages below specified levels. The SN75LPE185 functions properly during WAKE-UP mode, using the following power-supply conditions:

- (a) $V_{CC} = 4.75$ V, $V_{DD} = 9$ V, and $V_{SS} = -9$ V (data-sheet specifications)
- (b) $V_{CC} = 5 V$, $V_{DD} = 5 V$, and $V_{SS} = -5 V$
- (c) $V_{CC} = 5 V$, $V_{DD} =$ open, and $V_{SS} =$ open
- (d) $V_{CC} = 5 V$, $V_{DD} = 5 V$, and V_{SS} is shorted to the most negative supply.

Condition (a) describes the minimum supply voltages necessary for the device to comply fully to specifications.

Conditions (b) and (d) describe the condition where a -5-V supply is not available during auxiliary power. In this case, V_{SS} must be shorted to the most negative supply (i.e., GND or a voltage source close to, but below GND).

Condition (c) states V_{DD} and V_{SS} power supplies can be shut off.

In all cases, GND is understood to be 0 V, and the power supply voltages should never exceed the absolute maximum ratings.



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